

High Speed CMOS Logic Quad D-Type Flip-Flop, Three-State

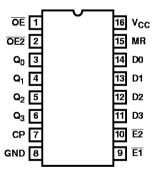
February 1998

Features

- · Three-State Buffered Outputs
- · Gated Input and Output Enables
- · Fanout (Over Temperature Range)
- Wide Operating Temperature Range ...-55°C to 125°C
- · Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- · HC Types
 - 2V to 6V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility,
 V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
 - CMOS Input Compatibility, $I_I \le 1\mu A$ at V_{OL} , V_{OH}

Pinout

CD74HC173, CD74HC173 (PDIP, SOIC) TOP VIEW



Description

The Harris CD74HC173 and CD74HCT173 high speed three-state quad D-type flip-flops are fabricated with silicon gate CMOS technology. They possess the low power consumption of standard CMOS Integrated circuits, and can operate at speeds comparable to the equivalent low power Schottky devices. The buffered outputs can drive 15 LSTTL loads. The large output drive capability and three-state feature make these parts ideally suited for interfacing with bus lines in bus oriented systems.

The four D-type flip-flops operate synchronously from a common clock. The outputs are in the three-state mode when either of the two output disable pins are at the logic "1" level. The input ENABLES allow the flip-flops to remain in their present states without having to disrupt the clock If either of the 2 input ENABLES are taken to a logic "1" level, the Q outputs are fed back to the inputs, forcing the flip-flops to remain in the same state. Reset is enabled by taking the MASTER RESET (MR) input to a logic "1" level. The data outputs change state on the positive going edge of the clock.

The CD74HCT173 logic family is functionally, as well as pin compatible with the standard 74LS logic family.

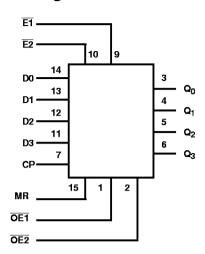
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC173E	-55 to 125	16 Ld PDIP	E16.3
CD74HCT173E	-55 to 125	16 Ld PDIP	E16.3
CD74HC173M	-55 to 125	16 Ld SOIC	M16.15
CD74HCT173M	-55 to 125	16 Ld SOIC	M16.15

NOTES:

- 1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
- Wafer and die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Functional Diagram



TRUTH TABLE

	INP				
		DATA E	NABLE	DATA	OUTPUT
MR	CP	E1	E2	D	Q _n
Н	Х	X	X	X	L
L	L	Х	Х	Х	Q_0
L	↑	Н	Х	Х	Q_0
L	↑	Х	Н	Х	Q_0
L	↑	L	L	L	L
L	↑	L	L	Н	Н

NOTE:

When either $\overline{\text{OE1}}$ or $\overline{\text{OE2}}$ (or both) is (are) high the output is disabled to the high-impedance state, however, sequential operation of the flip-flops is not affected.

H = High Voltage Level

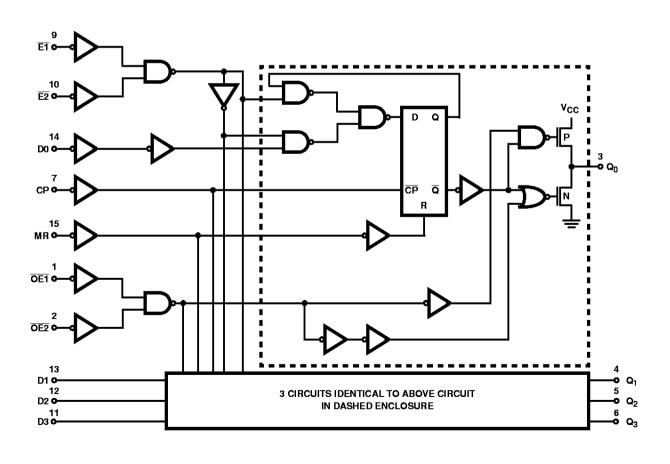
L = Low Voltage Level

X = Irrelevant

↑ = Transition from Low to High Level

 $\mathbf{Q}_0 = \mathsf{Level}$ Before the Indicated Steady-State Input Conditions Were Established

Logic Diagram



Absolute Maximum Ratings

Thermal Information

DC Supply Voltage, V _{CC} 0.5V to 7V
DC Input Diode Current, I _{IK}
For V _I < -0.5V or V _I > V _{CC} + 0.5V
DC Output Diode Current, IOK
For V _O < -0.5V or V _O > V _{CC} + 0.5V±20mA
DC Output Source or Sink Current per Output Pin, IO
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ ±25mA
DC V _{CC} or Ground Current, I _{CC} ±70mA

Thermal Resistance (Typical, Note 3)	θ _{JA} (°C/W)
PDIP Package	. 90
SOIC Package	. 160
Maximum Junction Temperature	
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(SOIC - Lead Tips Only)	

Operating Conditions

Temperature Range (T _A)55°C to 125°C Supply Voltage Range, V _{CC}
HC Types
HCT Types
DC Input or Output Voltage, V _I , V _O 0V to V _{CC}
Input Rise and Fall Time
2V
4.5V 500ns (Max)
6V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

			ST ITIONS		25 ⁰ C			-40°C TO 85°C		-55°C TO 125°C		
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	МАХ	UNITS
HC TYPES												
High Level Input	V _{IH}	-	-	2	1.5	ı	ı	1.5	-	1.5	-	V
Voltage				4.5	3.15	-	-	3.15	-	3.15	-	٧
				6	4.2	-	-	4.2	-	4.2	-	٧
Low Level Input Voltage	V _{IL}	-	-	2	1	•	0.5	•	0.5	-	0.5	٧
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	٧
				6	-	-	1.8	-	1.8	-	1.8	٧
High Level Output	V _{OH}	V _{IH} or	-0.02	2	1.9	-	-	1.9	-	1.9	-	٧
Voltage CMOS Loads		V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	٧
			-0.02	6	5.9	-	-	5.9	-	5.9	-	٧
High Level Output			-6	4.5	3.98	-	-	3.84	-	3.7	-	٧
Voltage TTL Loads			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output	V _{OL}	V _{IH} or	0.02	2	-	-	0.1	-	0.1	-	0.1	٧
Voltage CMOS Loads		V_{IL}	0.02	4.5	-	•	0.1		0.1		0.1	٧
			0.02	6			0.1		0.1		0.1	٧
Low Level Output	1		6	4.5	1	1	0.26	•	0.33	-	0.4	٧
Voltage TTL Loads			7.8	6	-	-	0.26	-	0.33	-	0.4	٧
Input Leakage Current	Ι _Ι	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μΑ
Quiescent Device Current	lcc	V _{CC} or GND	0	6	-	-	8	-	80	-	160	μΑ

DC Electrical Specifications (Continued)

			ST ITIONS	25 ⁰ C			-40°C T	O 85°C	-55°C TO 125°C			
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Three-State Leakage Current	loz	V _{IL} or V _{IH}	-	6	-	-	±0.5	-	±0.5	-	±10	μΑ
HCT TYPES												
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	٧
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	٧
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	٧
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	٧
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	٧
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	•	0.33	-	0.4	٧
Input Leakage Current	IJ	V _{CC} to GND	0	5.5	-	-	±0.1	-	±1	-	±1	μΑ
Quiescent Device Current	lcc	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μΑ
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	Δl _{CC}	V _{CC} -2.1	-	4.5 to 5.5	,	100	360	-	450	-	490	μА
Three-State Leakage Current	loz	V _{IL} or V _{IH}	-	5.5	-	-	±0.5	-	±5.0	-	±10	μА

NOTE:

HCT Input Loading Table

INPUT	UNIT LOADS				
D0-D3	0.15				
E1 and E2	0.15				
СР	0.25				
MR	0.2				
OE1 and OE2	0.5				

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360 μ A max at 25°C.

^{4.} For dual-supply systems theoretical worst case ($V_I = 2.4V$, $V_{CC} = 5.5V$) specification is 1.8mA.

Switching Specifications Input t_r , $t_f = 6 ns$

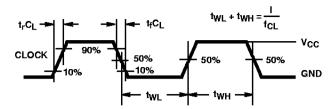
		TEST		25	°C	-40°C TO 85°C	-55°C TO 125°C]	
PARAMETER	SYMBOL	CONDITIONS	V _{CC} (V)	TYP	MAX	MAX	MAX	דואט:	
HC TYPES					•				
Propagation Delay, Clock to	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	200	250	300	ns	
Output			4.5	-	40	50	60	ns	
		C _L = 15pF	5	17	-	-	-	ns	
		CL = 50pF	6	-	34	43	51	ns	
Propagation Delay, MR to	t _{PHL}	C _L = 50pF	2	-	175	220	265	ns	
Output			4.5	-	35	44	53	ns	
		C _L = 15pF	5	12	-	-	-	ns	
		CL = 50pF	6	-	30	37	45	ns	
Propagation Delay Output Enable to Q (Figure 6)	t _{PLZ} , t _{PHZ}	CL = 50pF	2		150	190	225	ns	
	t _{PZL} , t _{PZH}	C _L = 50pF	4.5		30	38	45	ns	
		C _L = 15pF	5	12	-	-	-	ns	
		CL = 50pF	6		26	33	38	ns	
Output Transition Times	t _{TLH} , t _{THL}	C _L = 50pF	2	-	60	75	90	ns	
			4.5	-	12	15	18	ns	
			6	-	10	13	15	пѕ	
Maximum Clock Frequency	fMAX	C _L = 15pF	5	60	-	-	-	MH:	
Input Capacitance	C _{IN}	-	-	-	10	10	10	рF	
Three-State Output Capacitance	Co	-	-	-	10	10	10	рF	
Power Dissipation Capacitance (Notes 5, 6)	C _{PD}	-	5	29	-	-	-	pF	
HCT TYPES									
Propagation Delay, Clock to	t _{PLH} , t _{PHL}	C _L = 50pF	4.5	-	40	50	60	ns	
Output		C _L = 15pF	5	17	-	-	-	ns	
Propagation Delay, MR to	t _{PHL}	C _L = 50pF	4.5	-	44	55	66	ns	
Output		C _L = 15pF	5	18	-	-	-	пѕ	
Propagation Delay Output	t _{PZL} , t _{PZH}	CL = 50pF	2		150	190	225	пѕ	
Enable to Q (Figure 6)		C _L = 50pF	4.5		30	38	45	ns	
		C _L = 15pF	5	14	-	-	-	ns	
		CL = 50pF	6		26	33	38	ns	
Output Transition Times	t _{TLH} , t _{THL}	C _L = 50pF	4.5	-	15	19	22	пѕ	
Maximum Clock Frequency	f _{MAX}	C _L = 15pF	5	60	-	-	-	MH:	
Input Capacitance	C _{IN}	-	-	-	10	10	10	рF	
Power Dissipation Capacitance (Notes 5, 6)	C _{PD}	-	5	34	-	-	-	рF	

- 5. C_{PD} is used to determine the dynamic power consumption, per package.
 6. P_D = V_{CC}² f_i + ∑ (C_L V_{CC}² + f_O) where f_i = Input Frequency, f_O = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Prerequisite For Switching Specifications

			25	o _C	-40°C T	O 85°C	-55 ⁰ C T		
PARAMETER	SYMBOL	V _{CC} (V)	MIN	MAX	MIN	MAX	MIN	МАХ	UNITS
HC TYPES									
Maximum Clock Frequency	fMAX	2	6	-	5	-	4	-	MHz
		4.5	30	-	24	-	20	-	MHz
		6	35	-	28	-	24	-	MHz
MR Pulse Width	t _w	2	80	-	100	-	120	-	ns
		4.5	16	-	20	-	24	-	ns
		6	14	-	17	-	20	-	ns
Clock Pulse Width	t _w	2	80	-	100	-	120	-	ns
		4.5	16	-	20	-	24	-	ns
		6	14	-	17	-	20	-	ns
Set-up Time, Data to Clock	tsu	2	60	-	75	-	90	-	ns
and E to Clock		4.5	12	-	15	-	18	-	ns
		6	10	-	13	-	15	-	ns
Hold Time, Data to Clock	t _H	2	3	-	3	-	3	-	ns
		4.5	3	-	3	-	3	-	ns
		6	3	-	3	-	3	-	ns
Hold Time, E to Clock	t _H	2	0	-	0	-	0	-	ns
		4.5	0	-	0	-	0	-	ns
		6	0	-	0	-	0	-	ns
Removal Time, MR to Clock	t _{REM}	2	60	-	75	-	90	-	ns
		4.5	12	-	15	-	18	-	ns
		6	10	-	13	-	15	-	ns
HCT TYPES		•		•				•	
Maximum Clock Frequency	fMAX	4.5	20	-	16	-	13	-	MHz
MR Pulse Width	t _w	4.5	15	-	19	-	22	-	ns
Clock Pulse Width	t _w	4.5	25	-	31	-	38	-	ns
Set-up Time,	tsu	4.5	12	-	15	-	18	-	ns
Set-up Time, Data to Clock	tsu	4.5	18	-	23	-	27	-	ns
Hold Time, Data to Clock	t _H	4.5	0	-	0	-	0	-	ns
Hold Time, \overline{E} to Clock	t _H	4.5	0	-	0	-	0	-	ns
Removal Time, MR to Clock	tREM	4.5	12	-	15	-	18	-	ns

Test Circuits and Waveforms



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX} , input duty cycle = 50%.

FIGURE 1. HC CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

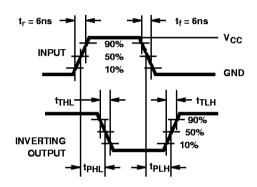


FIGURE 3. HC AND HCU TRANSITION TIMES AND PROPAGA-TION DELAY TIMES, COMBINATION LOGIC

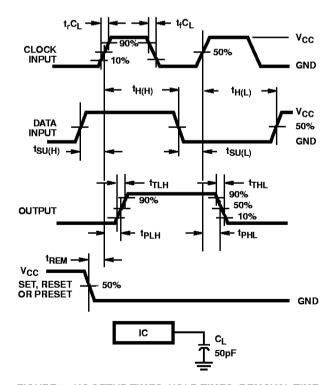
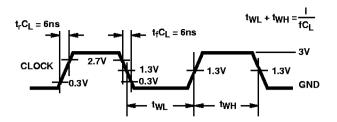


FIGURE 5. HC SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX} , input duty cycle = 50%.

FIGURE 2. HCT CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

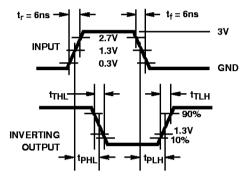


FIGURE 4. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

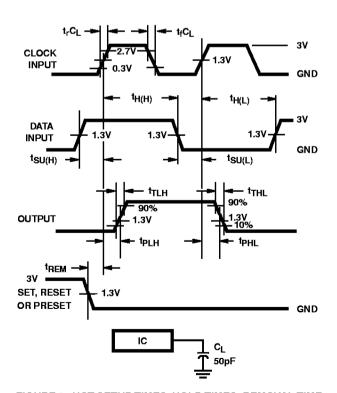
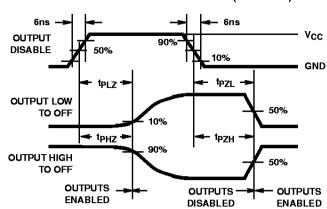


FIGURE 6. HCT SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

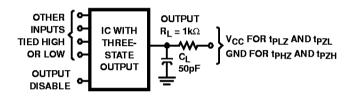
Test Circuits and Waveforms (Continued)



6ns **3V** OUTPUT DISABLE 0.3 GND tPLZ: ^tPZL **OUTPUT LOW** TO OFF 1.37 10% tPHZ = ^tPZH 90% **OUTPUT HIGH** TO OFF OUTPUTS OUTPUTS OUTPUTS **ENABLED** DISABLED **ENABLED**

FIGURE 7. HC THREE-STATE PROPAGATION DELAY WAVEFORM

FIGURE 8. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ to V_{CC} , $C_L = 50pF$.

FIGURE 9. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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